

RJK4514DPK

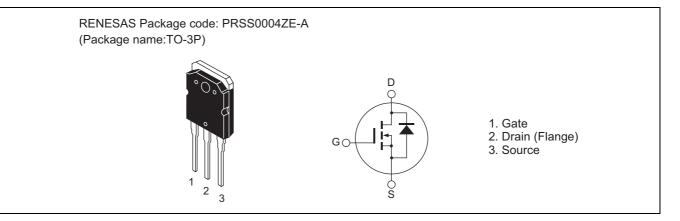
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1514-0100 Rev.1.00 Feb 13, 2007

Features

- Low on-resistance
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	450	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D	22	А
Drain peak current	Note1 I _{D (pulse)}	66	А
Body-drain diode reverse drain current	I _{DR}	22	А
Body-drain diode reverse drain peak current	I _{DR (pulse)} Note1	66	А
Avalanche current	I _{AP} ^{Note3}	5	А
Avalanche energy	E _{AR} ^{Note3}	1.4	mJ
Channel dissipation	Pch ^{Note2}	150	W
Channel to case thermal impedance	θch-c	0.833	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. $PW \le 10 \ \mu s$, duty cycle $\le 1\%$

2. Value at Tc = 25°C

3. STch = 25° C, Tch $\leq 150^{\circ}$ C



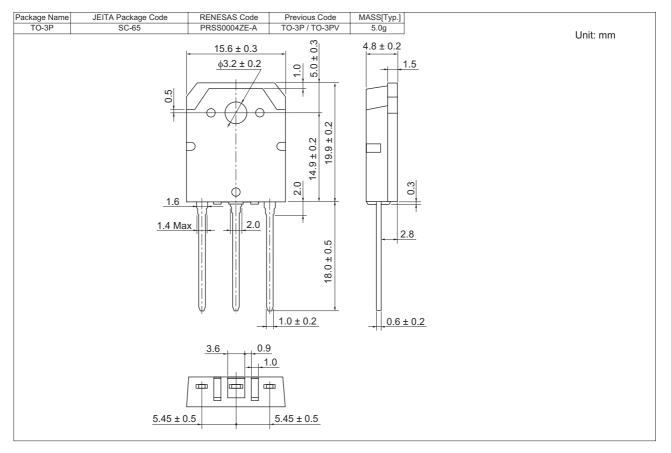
Electrical Characteristics

						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V _{(BR)DSS}	450		_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}	_	—	1	μΑ	$V_{DS} = 450 \text{ V}, \text{ V}_{GS} = 0$
Gate to source leak current	I _{GSS}	_	_	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	V _{GS(off)}	3.0	_	4.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state resistance	R _{DS(on)}		0.25	0.30	Ω	$I_D = 11 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
Input capacitance	Ciss	_	1800	_	pF	V _{DS} = 25 V
Output capacitance	Coss	_	200	—	pF	V _{GS} = 0 f = 1 MHz
Reverse transfer capacitance	Crss	_	27	—	pF	
Turn-on delay time	t _{d(on)}	_	35	—	ns	$I_{D} = 11 \text{ A} \\ V_{GS} = 10 \text{ V} \\ R_{L} = 20.5 \Omega \\ Rg = 10 \Omega$
Rise time	tr	_	58	—	ns	
Turn-off delay time	t _{d(off)}	_	95	—	ns	
Fall time	t _f	_	44	—	ns	
Total gate charge	Qg	_	46	—	nC	V _{DD} = 360 V
Gate to source charge	Qgs	_	10	_	nC	V _{GS} = 10 V I _D = 22 A
Gate to drain charge	Qgd	—	22	_	nC	
Body-drain diode forward voltage	V _{DF}	—	0.99	1.65	V	$I_F = 22 \text{ A}, V_{GS} = 0^{Note4}$
Body-drain diode reverse recovery time	t _{rr}	—	340	—	ns	$I_F = 22 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu \text{s}$

Notes: 4. Pulse test



Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK4514DPK-00-T0	360 pcs	Box (Tube)



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